

MJE15034 NPN, MJE15035 PNP

Preferred Device

Complementary Silicon Plastic Power Transistors TO-220, NPN & PNP Devices

... designed for use as high-frequency drivers in audio amplifiers.

- $h_{FE} = 100$ (Min) @ $I_C = 0.5$ Adc
= 10 (Min) @ $I_C = 2.0$ Adc
- Collector-Emitter Sustaining Voltage –
 $V_{CE(sus)} = 350$ Vdc (Min) – MJE15034, MJE15035
- High Current Gain – Bandwidth Product
 $f_T = 30$ MHz (Min) @ $I_C = 500$ mA dc
- TO-220AB Compact Package
- Epoxy meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Machine Model: C
Human Body Model: 3B

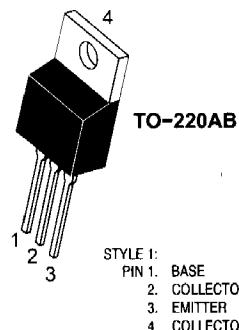
**4.0 AMPERES
POWER TRANSISTORS
COMPLEMENTARY
SILICON
350 VOLTS
50 WATTS**

MAXIMUM RATINGS

Rating	Symbol	MJE15034 MJE15035	Unit
Collector-Emitter Voltage	V_{CEO}	350	Vdc
Collector-Base Voltage	V_{CB}	350	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous – Peak	I_C	4.0 8.0	Adc
Base Current	I_B	1.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	50 0.40	Watts W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	2.0 0.016	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.5	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$



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